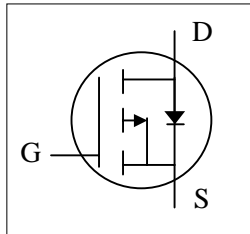




- ▼ 100% R_g & UIS Test
- ▼ Simple Drive Requirement
- ▼ Ultra Low On-resistance
- ▼ RoHS Compliant & Halogen-Free

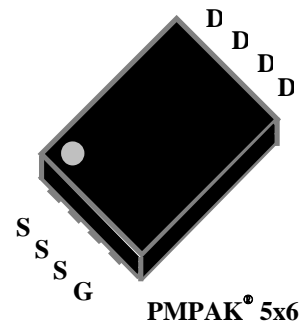


BV _{DSS}	-30V
R _{DS(ON)}	3mΩ
I _D ⁴	-125A

Description

AP3P3R0 series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The PMPAK[®] 5x6 package is special for voltage conversion application using standard infrared reflow technique with the backside heat sink to achieve the good thermal performance.



Absolute Maximum Ratings @T_j=25°C (unless otherwise specified)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Drain Current (Chip), V _{GS} @ 10V ⁴	-125	A
I _D @T _C =25°C	Drain Current, V _{GS} @ 10V ⁴ (Package Limited)	-60	A
I _D @T _A =25°C	Drain Current ³ , V _{GS} @ 10V	-33.5	A
I _D @T _A =70°C	Drain Current ³ , V _{GS} @ 10V	-26.8	A
I _{DM}	Pulsed Drain Current ¹	-200	A
P _D @T _C =25°C	Total Power Dissipation	69.4	W
P _D @T _A =25°C	Total Power Dissipation	5	W
E _{AS}	Single Pulse Avalanche Energy ⁵	45	mJ
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Unit
R _{thj-c}	Maximum Thermal Resistance, Junction-case	1.8	°C/W
R _{thj-a}	Maximum Thermal Resistance, Junction-ambient ³	25	°C/W



AP3P3R0MT

Electrical Characteristics @ $T_j=25^{\circ}\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-20A$	-	-	3	$m\Omega$
		$V_{GS}=-4.5V, I_D=-10A$	-	-	4.5	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-	-3	V
g_{fs}	Forward Transconductance	$V_{DS}=-5V, I_D=-20A$	-	67	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-24V, V_{GS}=0V$	-	-	-10	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Q_g	Total Gate Charge	$I_D=-20A$	-	76	122	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=-15V$	-	24	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=-4.5V$	-	26	-	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=-15V$	-	19	-	ns
t_r	Rise Time	$I_D=-1A$	-	12	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega$	-	160	-	ns
t_f	Fall Time	$V_{GS}=-10V$	-	74	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	9400	15040	pF
C_{oss}	Output Capacitance	$V_{DS}=-15V$	-	1230	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	680	-	pF
R_g	Gate Resistance	$f=1.0\text{MHz}$	-	3	6	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_S=-20A, V_{GS}=0V$	-	-	-1.2	V
t_{rr}	Reverse Recovery Time	$I_S=-20A, V_{GS}=0V,$	-	36	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu s$	-	30	-	nC

Notes:

1. Pulse width limited by Max. junction temperature.
2. Pulse test
3. Surface mounted on 1 in² copper pad of FR4 board, $t \leq 10\text{sec}$
4. Package limitation current is 60A .
5. Starting $T_j=25^{\circ}\text{C}$, $V_{DD}=-30V$, $L=0.1\text{mH}$, $R_G=25\Omega$

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

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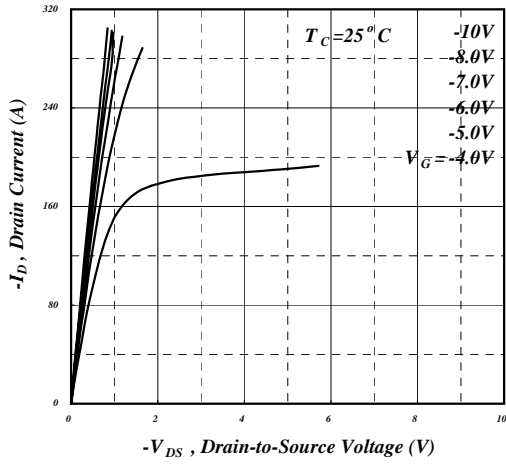


Fig 1. Typical Output Characteristics

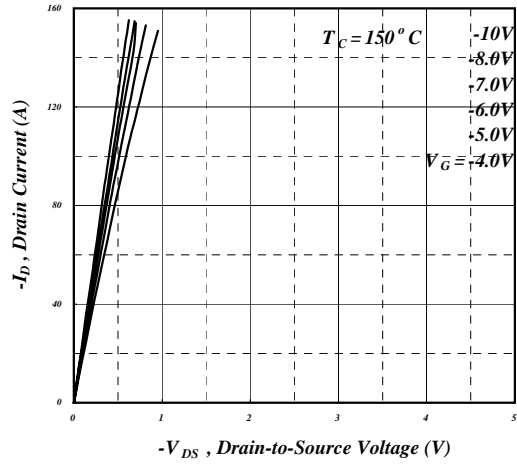


Fig 2. Typical Output Characteristics

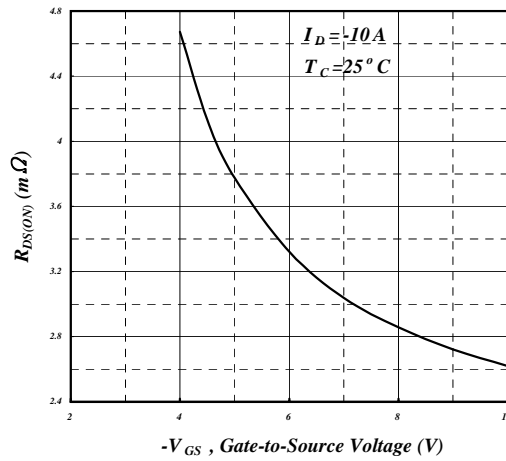


Fig 3. On-Resistance v.s. Gate Voltage

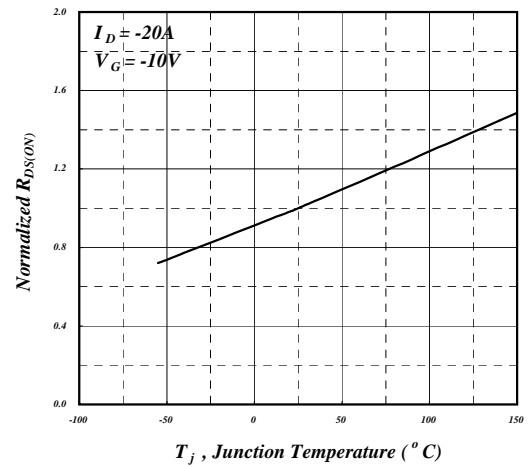


Fig 4. Normalized On-Resistance v.s. Junction Temperature

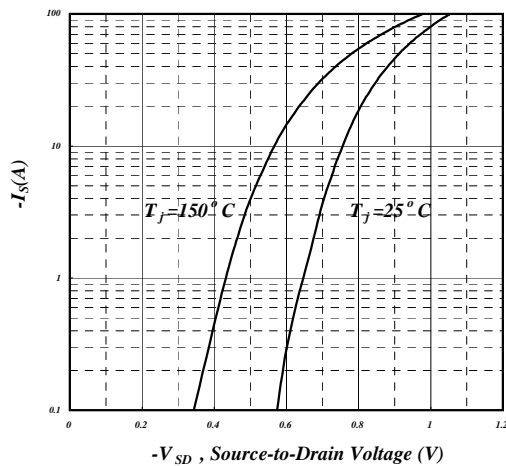


Fig 5. Forward Characteristic of Reverse Diode

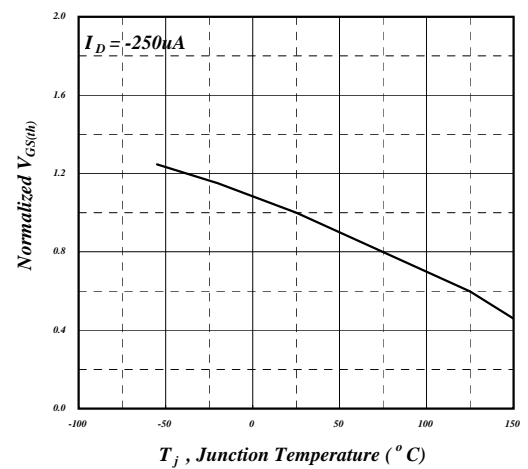


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

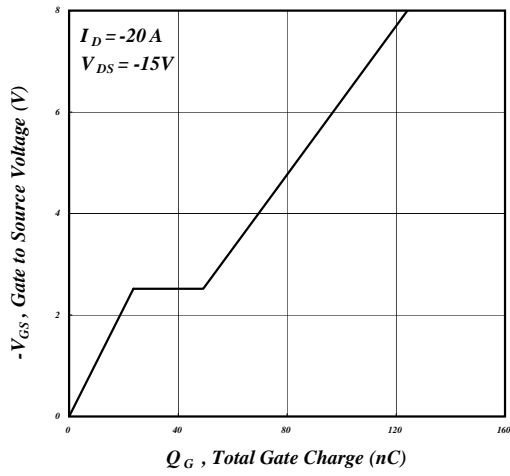


Fig 7. Gate Charge Characteristics

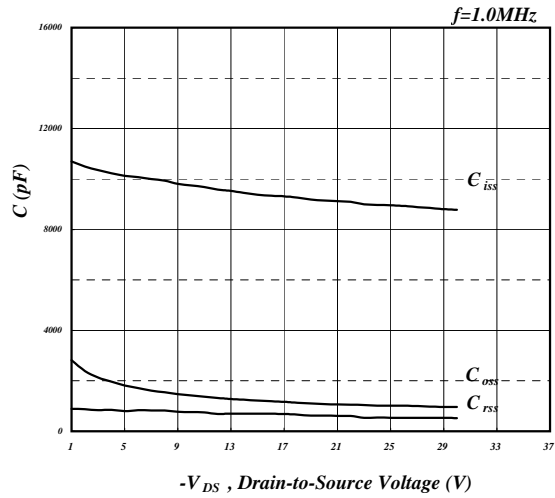


Fig 8. Typical Capacitance Characteristics

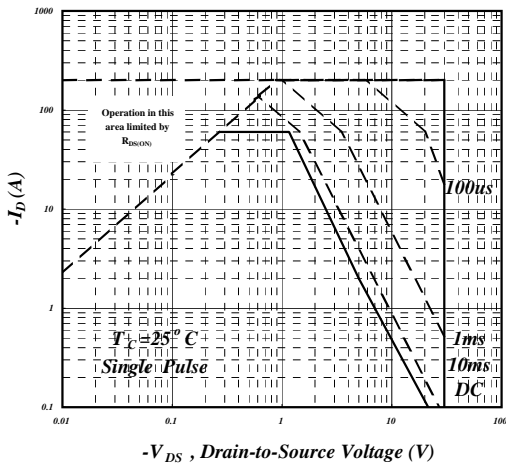


Fig 9. Maximum Safe Operating Area

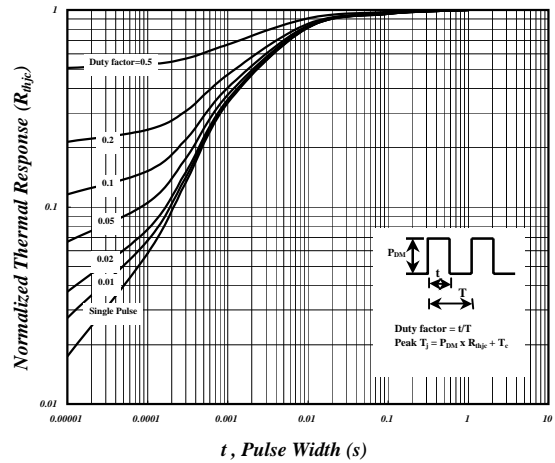


Fig 10. Effective Transient Thermal Impedance

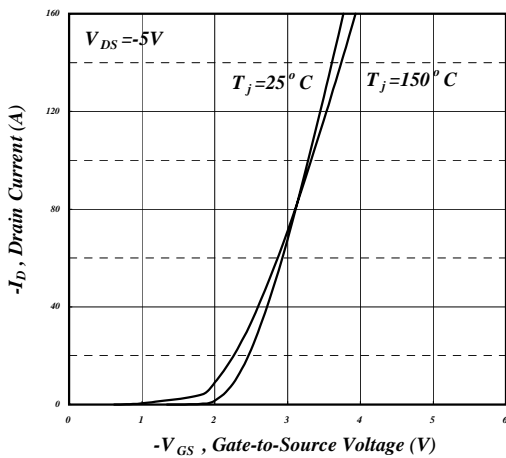


Fig 11. Transfer Characteristics

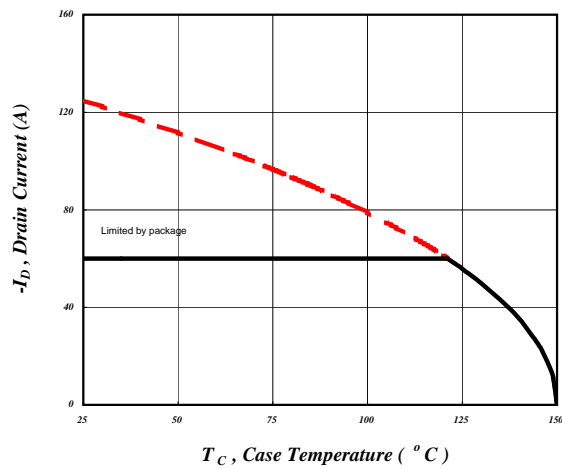


Fig 12. Drain Current v.s. Case Temperature

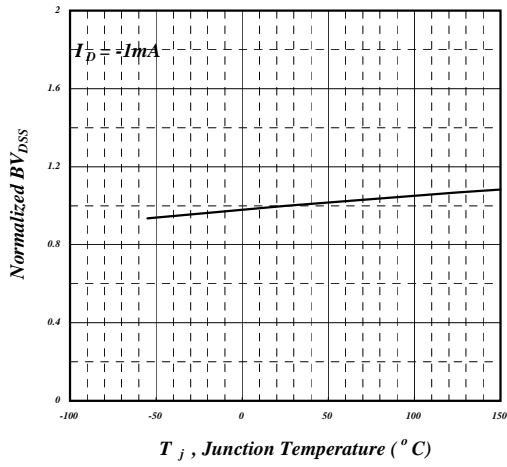


Fig 13. Normalized BV_{DSS} v.s. Junction Temperature

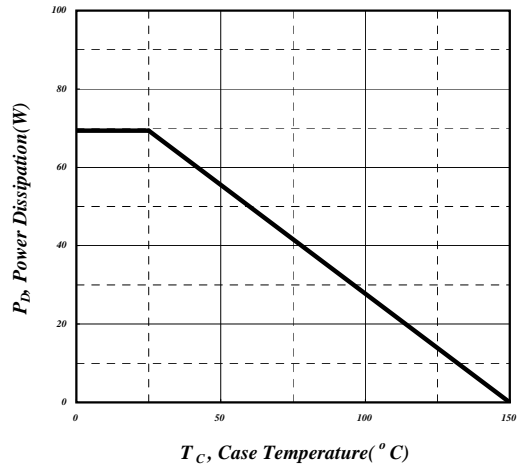


Fig 14. Total Power Dissipation

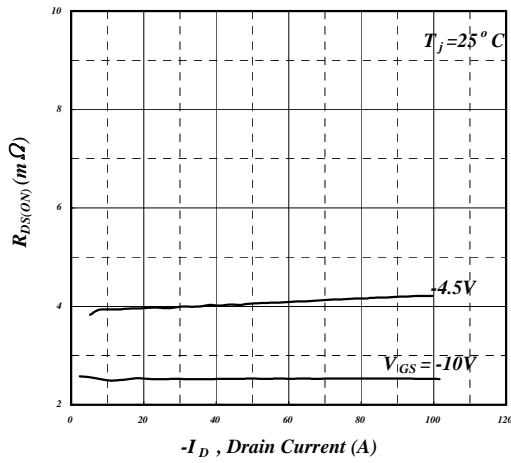


Fig 15. Typ. Drain-Source on State Resistance



AP3P3R0MT

MARKING INFORMATION

